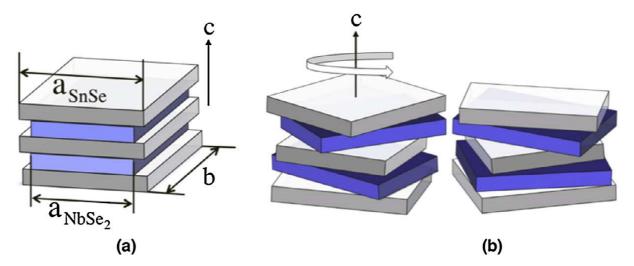
## Structural and electrical properties of a new ([SnSe]<sub>1.16</sub>)<sub>m</sub>(NbSe<sub>2</sub>)<sub>1</sub> polytype

M. B. Alemayehu, M. Falmbigl, C. Grosse, K. Ta, S. F. Fischer, and D. C. Johnson J. Alloys Compd. **619**, 861-868 (2015).

## **Short Abstract**

A new polytype of the misfit layer compound ( $[SnSe]_{1.16}$ )<sub>1</sub>( $NbSe_2$ )<sub>1</sub> with extensive rotational disorder was prepared from designed modulated elemental reactants. This polytype, previously referred to as a ferecrystal, formed over a range of compositions and precursor thicknesses. The *a*- and *b*-axis inplane lattice parameters of both the SnSe and  $NbSe_2$  constituents were unequal. The ferecrystalline compound is 1.6 times more conductive than the misfit layer compound. Hall effect measurements indicate that the ferecrystal is a *p*-type metal and that the higher conductivity is due to the higher mobility of carriers in the ferecrystalline compound.



**Above.** A schematic representation of the structure of the ([SnSe]<sub>1.16</sub>)<sub>1</sub>(NbSe<sub>2</sub>)<sub>1</sub> misfit layer compound (a) and two grains of the ([SnSe]<sub>1.16</sub>)<sub>1</sub>(NbSe<sub>2</sub>)<sub>1</sub> ferecrystal compound (b) illustrating the extensive rotational disorder between the constituent layers.